1 Scope

The present specifications shall apply to Sanken silicon diode, RM1Z.

2 Outline

Туре	Silicon Rectifier Diode (Mesa type)				
Structure	Resin Molded Flammability: UL94V-0 (Equivalent)				
Applications	Frequency Rectification, etc.				

3 Absolute maximum ratings

8-						
No.	Item	Symbol	Unit	Rating	Conditions	
1	Transient Peak Reverse Voltage	V _{RSM}	V	250		
2	Peak Reverse Voltage	V _{RM}	V	200		
3	Average Forward Current	I _{F(AV)}	А	1.0	Refer to derating curve in Section 6	
4	Peak Surge Forward Current	I _{FSM}	А	50	50Hz. Half sinewave, one	
5	Junction Temperature	Tj	°C	-40 to +150		
6	Storage Temperature	T _{stg}	°C	-40 to +150		

4 Electrical characteristics (Ta=25°C, unless otherwise specified)

No.	Item	Symbol	Unit	Rating	Conditions
1	Forward Voltage Drop	\mathbf{V}_{F}	V	0.95 max.	I _F =1.0A
2	Reverse Leakage Current	I _R	μΑ	5 max.	V _R =V _{RM}
3 Reverse Leakage Current Under High Temperature		H∙I _R	μΑ	50 max.	$V_R = V_{RM}, T_j = 100^{\circ}C$
4	Thermal Resistance	R _{th(j-l)}	°C/W	15 max.	Between Junction and Lead



